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With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!




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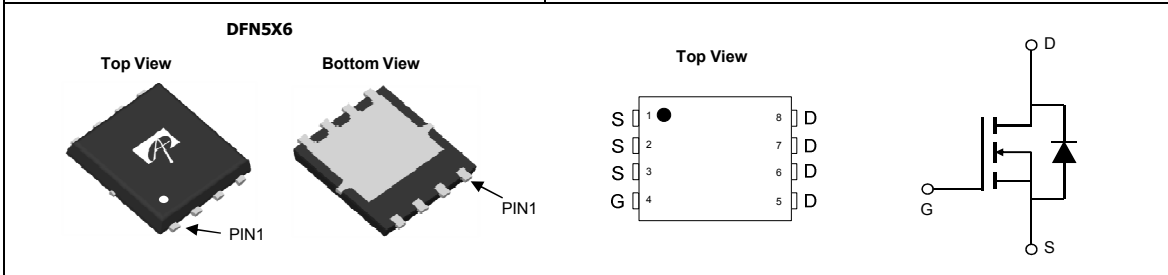
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General Description	Product Summary								
<ul style="list-style-type: none"> <li>• Latest Trench Power AlphaMOS (αMOS LV) technology</li> <li>• Low <math>R_{DS(ON)}</math></li> <li>• Low Gate Charge</li> <li>• High Current Capability</li> <li>• RoHS and Halogen-Free Compliant</li> </ul>	<table> <tr> <td><math>V_{DS}</math></td> <td>30V</td> </tr> <tr> <td><math>I_D</math> (at <math>V_{GS}=10V</math>)</td> <td>200A</td> </tr> <tr> <td><math>R_{DS(ON)}</math> (at <math>V_{GS}=10V</math>)</td> <td>&lt; 0.68mΩ</td> </tr> <tr> <td><math>R_{DS(ON)}</math> (at <math>V_{GS}=4.5V</math>)</td> <td>&lt; 1.1mΩ</td> </tr> </table>	$V_{DS}$	30V	$I_D$ (at $V_{GS}=10V$ )	200A	$R_{DS(ON)}$ (at $V_{GS}=10V$ )	< 0.68mΩ	$R_{DS(ON)}$ (at $V_{GS}=4.5V$ )	< 1.1mΩ
$V_{DS}$	30V								
$I_D$ (at $V_{GS}=10V$ )	200A								
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$R_{DS(ON)}$ (at $V_{GS}=4.5V$ )	< 1.1mΩ								
<b>Application</b> <ul style="list-style-type: none"> <li>• High performance ORing, Efuse</li> <li>• Ultra high current battery charge/discharge</li> </ul>	100% UIS Tested 100% Rg Tested 								



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AON6560	DFN 5x6	Tape & Reel	3000

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted				
Parameter	Symbol	Maximum	Units	
Drain-Source Voltage	$V_{DS}$	30	V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V	
Continuous Drain Current <sup>G</sup>	$I_D$	$T_C=25^\circ\text{C}$	200	A
		$T_C=100^\circ\text{C}$	200	
Pulsed Drain Current <sup>C</sup>	$I_{DM}$	800		
Continuous Drain Current	$I_{DSM}$	$T_A=25^\circ\text{C}$	84	A
		$T_A=70^\circ\text{C}$	67	
Avalanche Current <sup>C</sup>	$I_{AS}$	80	A	
Avalanche energy	$E_{AS}$	160	mJ	
$V_{DS}$ Spike	$V_{SPIKE}$	36	V	
Power Dissipation <sup>B</sup>	$P_D$	$T_C=25^\circ\text{C}$	208	W
		$T_C=100^\circ\text{C}$	83	
Power Dissipation <sup>A</sup>	$P_{DSM}$	$T_A=25^\circ\text{C}$	7.3	W
		$T_A=70^\circ\text{C}$	4.7	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$	

Thermal Characteristics				
Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	$t \leq 10s$	14	$^\circ\text{C/W}$
Maximum Junction-to-Ambient <sup>A D</sup>		Steady-State	40	$^\circ\text{C/W}$
Maximum Junction-to-Case	$R_{\theta JC}$	0.46	0.6	$^\circ\text{C/W}$

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	ID=250μA, VGS=0V	30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			1 5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.4	1.8	2.2	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =20A T <sub>J</sub> =125°C		0.55	0.68	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A		0.85	1.1	
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =20A		100		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.65	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current <sup>6</sup>				200	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, f=1MHz		11500		pF
C <sub>oss</sub>	Output Capacitance			3400		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			3100		pF
R <sub>g</sub>	Gate resistance	f=1MHz		1.2		Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g</sub> (10V)	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, I <sub>D</sub> =20A		230	325	nC
Q <sub>g</sub> (4.5V)	Total Gate Charge			130	185	
Q <sub>gs</sub>	Gate Source Charge			28		
Q <sub>gd</sub>	Gate Drain Charge			92		
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, R <sub>L</sub> =0.75Ω, R <sub>GEN</sub> =3Ω		16		ns
t <sub>r</sub>	Turn-On Rise Time			42		
t <sub>D(off)</sub>	Turn-Off DelayTime			115.5		
t <sub>f</sub>	Turn-Off Fall Time			91.5		
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =20A, dI/dt=500A/μs		38.5		ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =20A, dI/dt=500A/μs		120		nC

A. The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C. The Power dissipation P<sub>DSM</sub> is based on R<sub>θJA</sub> ≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Single pulse width limited by junction temperature T<sub>J(MAX)</sub>=150° C.

D. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to case R<sub>θJC</sub> and case to ambient.

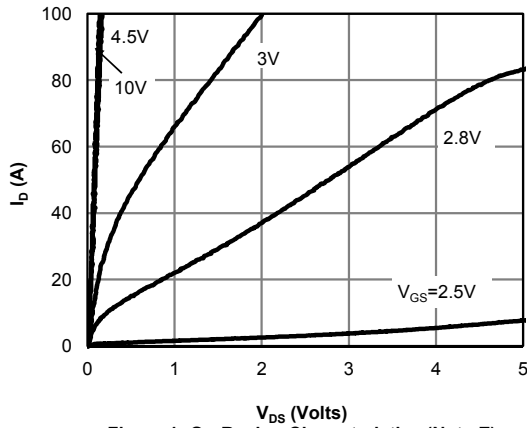
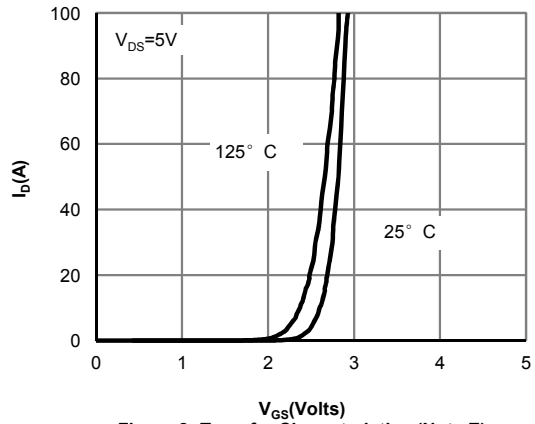
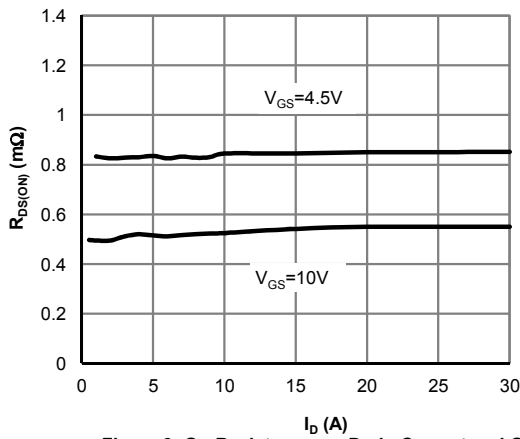
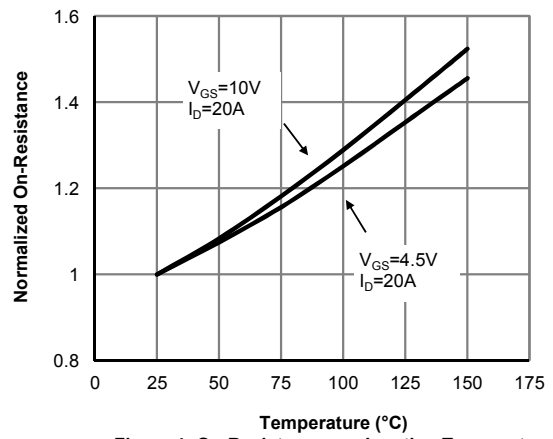
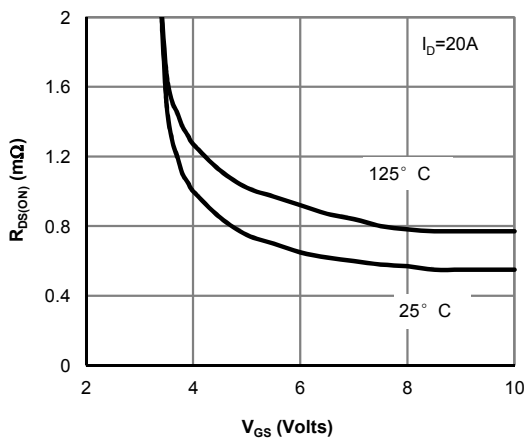
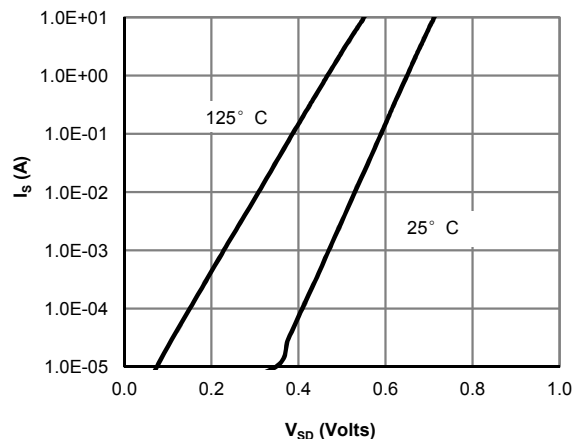
E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T<sub>J(MAX)</sub>=150° C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

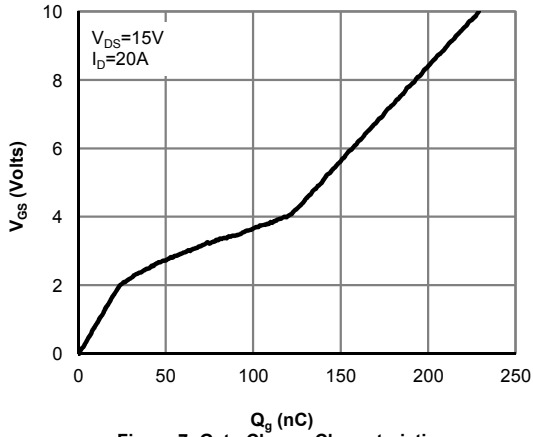
H. These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25° C.

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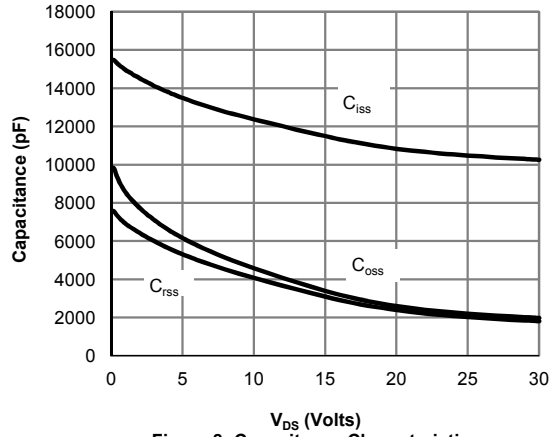
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

**Figure 1: On-Region Characteristics (Note E)**

**Figure 2: Transfer Characteristics (Note E)**

**Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)**

**Figure 4: On-Resistance vs. Junction Temperature (Note E)**

**Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)**

**Figure 6: Body-Diode Characteristics (Note E)**



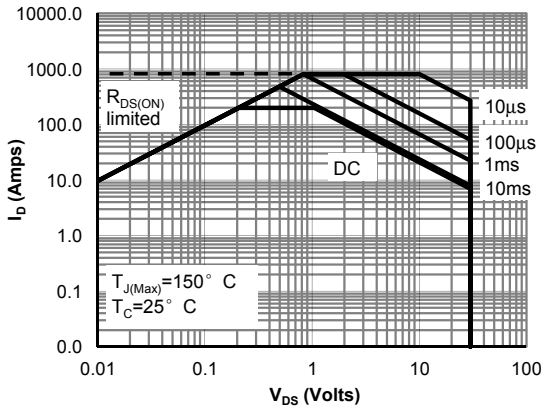
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



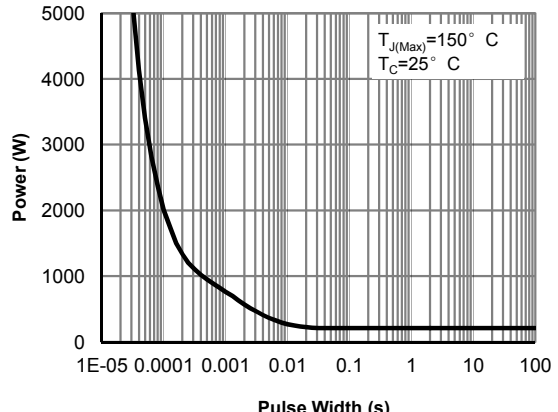
**Figure 7: Gate-Charge Characteristics**



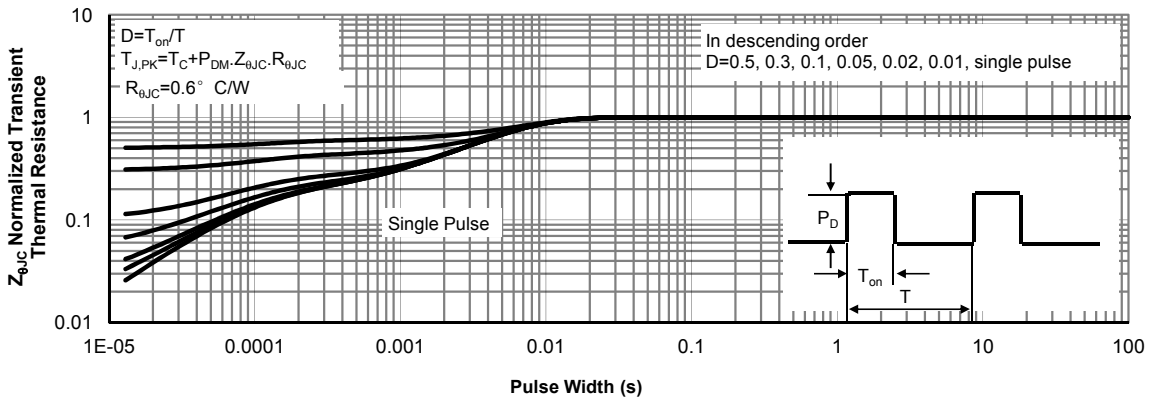
**Figure 8: Capacitance Characteristics**



**Figure 9: Maximum Forward Biased Safe Operating Area (Note F)**



**Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)**



**Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)**

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

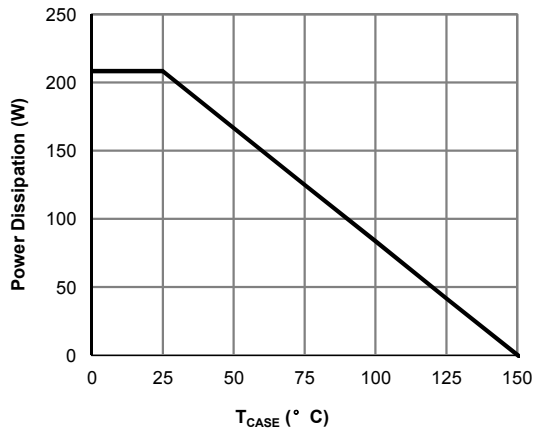


Figure 12: Power De-rating (Note F)

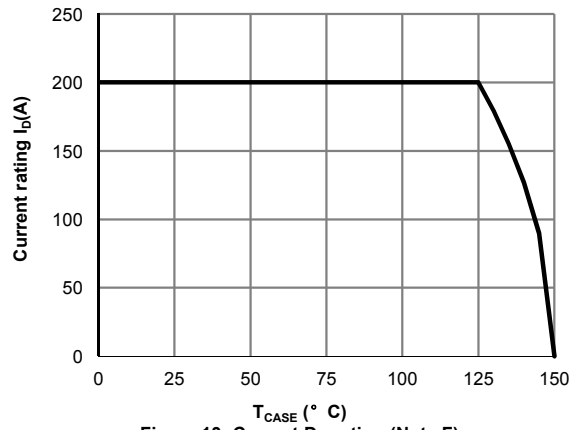


Figure 13: Current De-rating (Note F)

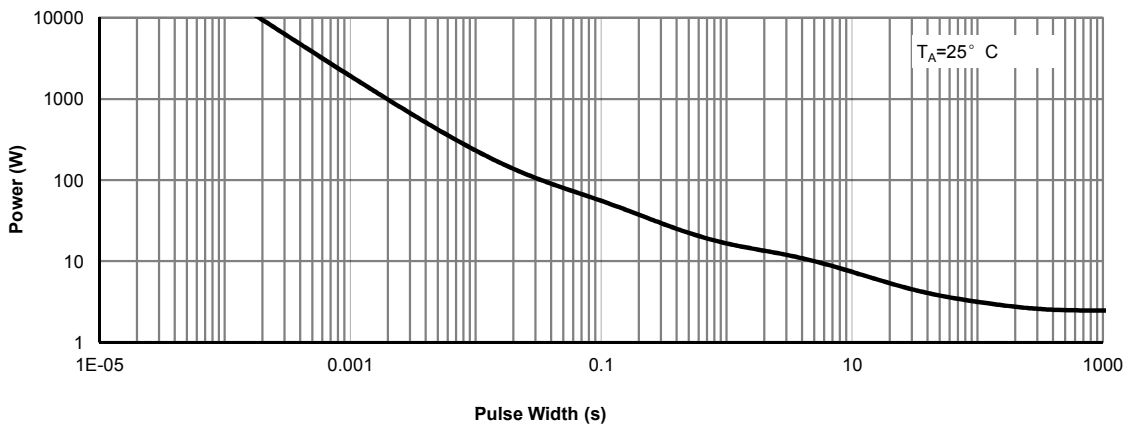


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note H)

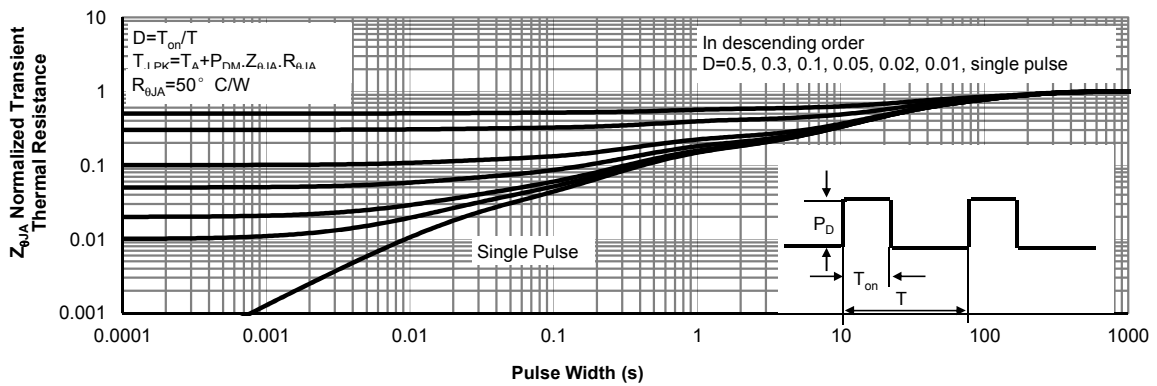
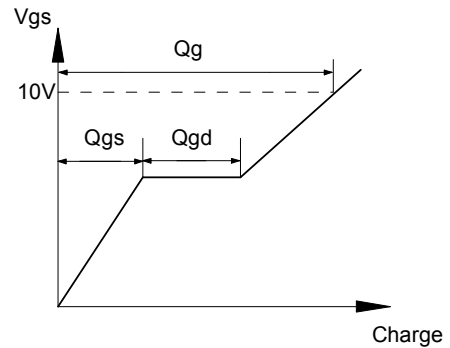
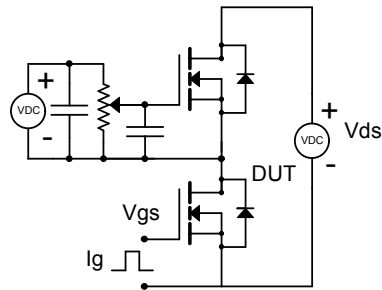
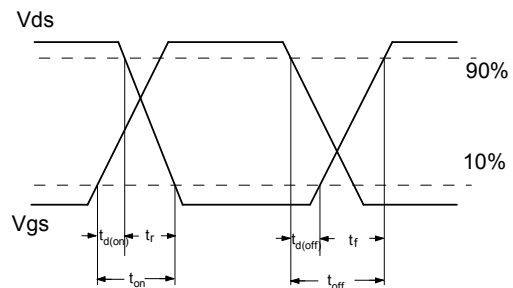
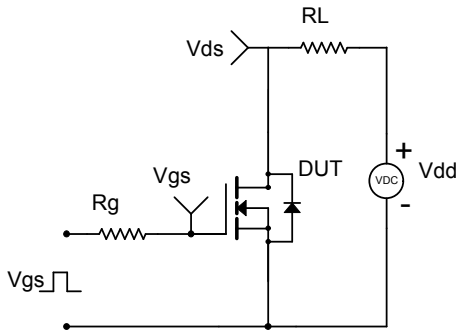


Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)

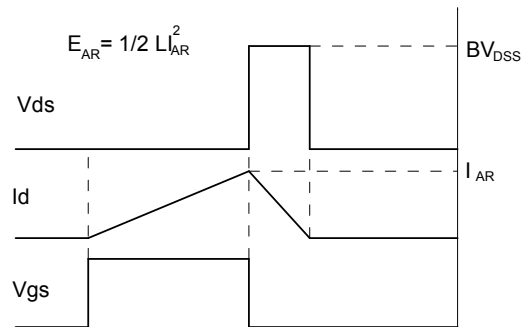
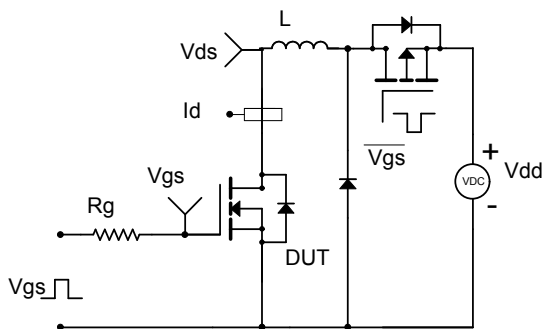
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

